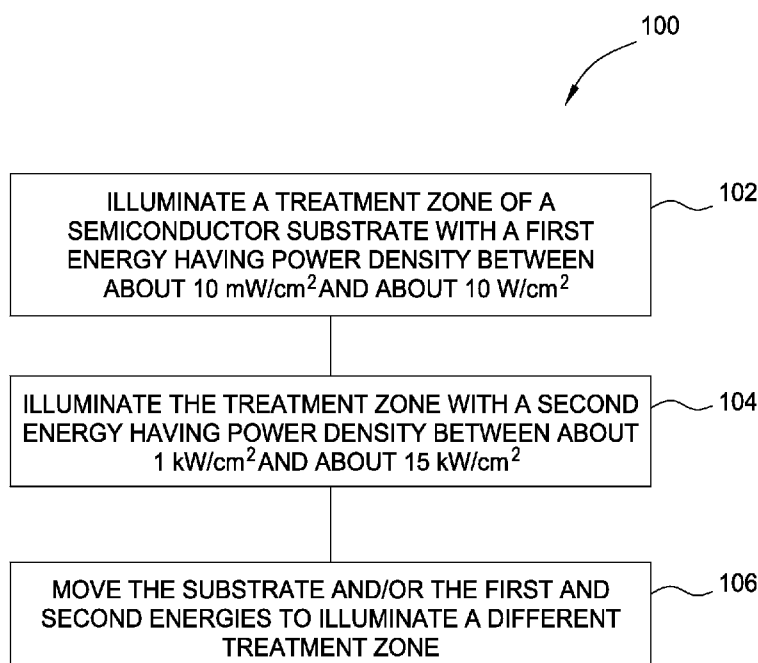




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[Continued on next page]

(54) Title: DUAL WAVELENGTH ANNEALING METHOD AND APPARATUS



(57) Abstract: Methods and apparatus for thermal processing of semiconductor substrates are described. A solid state radiant emitter is used to provide a field of thermal processing energy. A second solid state radiant emitter is used to provide a field of activating energy. The thermal processing energy and the activating energy are directed to a treatment zone of the substrate, where the activating energy increases absorption of the thermal processing radiation in the substrate, resulting in thermal processing of the substrate in the areas illuminated by the activating energy.

FIG. 1



SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, —
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